

## Radiation-Hardened 5-Channel Bus Transceiver with cold sparing

### 1 GENERAL DESCRIPTION

The AP54RHC506 is a radiation-hardened by design **5-bit bus transceiver with 3-state outputs** that is ideally suited for commercial space and other applications demanding radiation tolerance and high reliability. It is fabricated in a 180 nm CMOS process utilizing proprietary radiation-hardening techniques, delivering high resiliency to single-event effects (SEE) and to a total ionizing dose (TID) up to **30 krad (Si) at 5 V** and **70 krad (Si) at 3.3 V**.

This device is a member of the Apogee Semiconductor **AP54RHC logic family** operating across a voltage supply range of **1.65 V to 5.5 V**.

An output enable control pin allows all buffers to be placed in a high impedance (high-Z) state, simplifying usage in applications with shared busses or mixed power domains. A direction control pin is used to determine whether data flow is A→B or B→A.

Zero-power penalty™ cold sparing is supported, along with Class 2 ESD protection on all inputs and outputs. A proprietary output stage and robust power-on reset (POR) circuit allow the AP54RHC506 to be cold-spared in any redundant configuration with no static power loss on any pad of the device. The redundant output stage also features a high drive capability with low static power loss.

The AP54RHC506 also features a triple-redundant design throughout its entire circuitry, which allows it to be immune to single-event transients (SET) without requiring additional redundant devices.

Ordering information may be found in Table 9 on Page 13.

### 1.1 FEATURES

- 1.65 VDC to 5.5 VDC operation
- Inputs tolerant up to 5.5 VDC at any V<sub>CC</sub>
- Provides logic-level down translation to V<sub>CC</sub>
- Extended operating temperature range (-55 °C to +125 °C)
- Proprietary **cold sparing capability** with **zero** static power penalty
- **Built-in triple redundancy** for enhanced reliability
- Internal power-on reset (POR) circuitry ensures reliable power up and power down responses during hot plug and cold sparing operations
- Tri-state output drivers
- Class 2 ESD protection (4000 V HBM, 500 V CDM)
- TID resilience of **30 krad (Si)** assured at 5.5 V and characterized to **70 krad (Si)** at 3.3 V
- SEL immune to LET of **80 MeV-cm<sup>2</sup>/mg**
- Meets NASA's ASTM E595 outgassing specification

### 1.2 LOGIC DIAGRAM

The AP54RHC506 logic function is shown below:

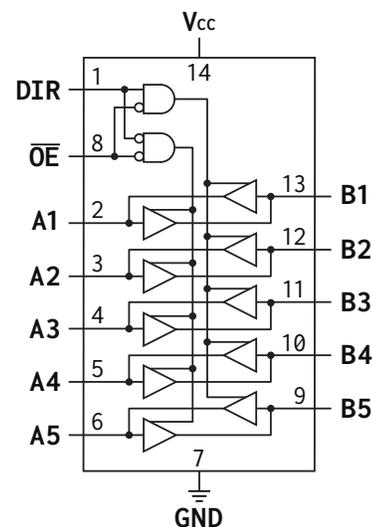


Figure 1: AP54RHC506 Logic Diagram

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## 2 ACRONYMS AND ABBREVIATIONS

ESD	Electrostatic Discharge
POR	Power On Reset
RHA	Radiation Hardness Assurance
SEE	Single Event Effects
SEL	Single Event Latchup
SET	Single Event Transient
TID	Total Ionizing Dose
TMR	Triple Modular Redundancy
CDM	Charged-device Model
HBM	Human-body Model

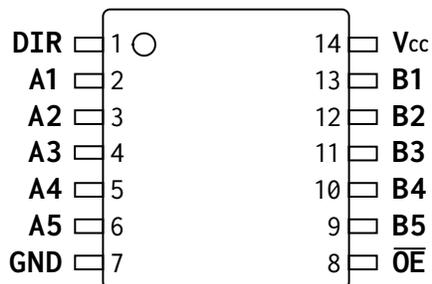
### 3 LOGIC DATA

The AP54RHC506 truth table is found in Table 1. **H** indicates HIGH logic level, **L** indicates LOW logic level, **X** indicates DON'T CARE and **Z** indicates HIGH-Z (TRI-STATE).

**Table 1:** AP54RHC506 Device Truth Table

EN	DIR	Function
H	X	All buffers tri-state (HIGH-Z)
L	L	A bus to B bus
L	H	B bus to A bus

### 4 PIN CONFIGURATION



**Figure 2:** AP54RHC506 Device Pinout

**Table 2:** AP54RHC506 Device Pinout

PIN NAME(S)	PIN NUMBER(S)	DESCRIPTION
A1, A2, A3, A4, A5	2, 3, 4, 5, 6	A Side Inputs (DIR = L) or 3-State Outputs (DIR = H)
B1, B2, B3, B4, B5	13, 12, 11, 10, 9	B Side Inputs (DIR = H) or 3-State Outputs (DIR = L)
DIR	1	Direction Control Input
$\overline{OE}$	8	Output Enable (active-low)
V <sub>CC</sub>	14	Positive Voltage Supply
GND	7	Ground

## 5 ELECTRICAL CHARACTERISTICS

The sign convention for current follows JEDEC standards with negative values representing current sourced from the device and positive values representing current sunk into the device.

### 5.1 ABSOLUTE MAXIMUM RATINGS

Excursions beyond the values listed in Table 3 may cause permanent damage to the device. Proper function of the device cannot be guaranteed if these values are exceeded, and long-term device reliability may be affected. Functionality of the device at these values, or beyond those listed in [Recommended Operating Conditions](#) (Table 4) is not guaranteed.

All parameters are specified across the entire operating temperature range unless otherwise specified.

**Table 3:** Absolute Maximum Ratings

SYMBOL	PARAMETER	VALUE	UNITS	
$V_{CC}$	Supply Voltage	-0.5 to +5.5	V	
$V_I$	Input voltage range	-0.5 to +5.5	V	
$V_O$	Output voltage range	-0.5 to $V_{CC} + 0.5^{(1)}$	V	
$I_{IK} (V_I < 0)$	Input clamp current	100	mA	
$I_O$	Continuous output current (per pin)	100	mA	
$I_{CC}$	Maximum supply current	100	mA	
$V_{ESD}$	ESD Voltage	HBM	4000	V
		CDM	500	V
$T_J$	Operating junction temperature range	-55 to +150	°C	
$T_{STG}$	Storage temperature range	-65 to +150	°C	

<sup>(1)</sup>  $V_O$  must remain below absolute maximum rating of  $V_{CC}$

**5.2 RECOMMENDED OPERATING CONDITIONS**

All recommended parameters below are specified across the entire operating temperature range unless otherwise specified.

**Table 4:** Recommended Operating Conditions

SYMBOL	PARAMETER	MIN	MAX	UNITS	
$V_{CC}$	Supply voltage	1.65	5.5	V	
$V_I$	Input voltage range	0	5.5	V	
$V_O$	Output voltage range	0	$V_{CC}$	V	
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 1.65$ to $1.95$ V	1.4	-	V
		$V_{CC} = 2.3$ to $2.7$ V	1.9	-	
		$V_{CC} = 3.0$ to $3.6$ V	2.5	-	
		$V_{CC} = 4.5$ to $5.5$ V	3.8	-	
$V_{IL}$	LOW-level input voltage	$V_{CC} = 1.65$ to $1.95$ V	-	0.4	V
		$V_{CC} = 2.3$ to $2.7$ V	-	0.6	
		$V_{CC} = 3.0$ to $3.6$ V	-	0.9	
		$V_{CC} = 4.5$ to $5.5$ V	-	1.35	
$I_{OH}$	HIGH-level output current	$V_{CC} = 1.65$ to $1.95$ V	-	-4	mA
		$V_{CC} = 2.3$ to $2.7$ V	-	-8	
		$V_{CC} = 3.0$ to $3.6$ V	-	-16	
		$V_{CC} = 4.5$ to $5.5$ V	-	-24	
$I_{OL}$	LOW-level output current	$V_{CC} = 1.65$ to $1.95$ V	-	4	mA
		$V_{CC} = 2.3$ to $2.7$ V	-	8	
		$V_{CC} = 3.0$ to $3.6$ V	-	16	
		$V_{CC} = 4.5$ to $5.5$ V	-	24	
$t_r, t_f$	Input rise or fall time (10% - 90%)	$V_{CC} = 1.65$ to $1.95$ V	-	1000	ns
		$V_{CC} = 2.3$ to $2.7$ V	-	600	
		$V_{CC} = 3.0$ to $3.6$ V	-	500	
		$V_{CC} = 4.5$ to $5.5$ V	-	400	

**Table 5:** Thermal Information

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS
$T_J$	Operating junction temperature	-55	-	+125	°C
$R_{\theta JA}$	Junction to ambient thermal resistance	-	100	-	°C/W

### 5.3 STATIC CHARACTERISTICS

All parameters are specified across the entire operating temperature range unless otherwise specified.

**Table 6:** DC Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	V <sub>CC</sub>	MIN	TYP	MAX	UNITS
V <sub>OL</sub>	LOW-Level Output Voltage	I <sub>O</sub> = 100 μA	1.65 to 5.5 V	-	0.02	0.05	V
		I <sub>O</sub> = 1 mA	1.65 to 5.5 V	-	0.05	0.15	V
		I <sub>O</sub> = 4 mA	1.65 V	-	0.27	0.8	V
			2.3 V	-	0.3	0.6	V
			3.0 V	-	0.2	0.4	V
			4.5 V	-	0.2	0.4	V
		I <sub>O</sub> = 8 mA	2.3 V	-	0.6	1.0	V
			3.0 V	-	0.4	0.8	V
			4.5 V	-	0.3	0.6	V
		I <sub>O</sub> = 16 mA	3.0 V	-	1.0	1.4	V
4.5 V	-		1.1	1.5	V		
I <sub>O</sub> = 24 mA	4.5 V	-	1.1	1.5	V		
V <sub>OH</sub>	HIGH-Level Output Voltage	I <sub>O</sub> = -100 μA	1.65 to 5.5 V	V <sub>CC</sub> - 0.1	V <sub>CC</sub> - 0.02	-	V
		I <sub>O</sub> = -1 mA	1.65 to 5.5 V	V <sub>CC</sub> - 0.15	V <sub>CC</sub> - 0.08	-	V
		I <sub>O</sub> = -4 mA	1.65 V	1.0	1.35	-	V
			2.3 V	1.8	2.0	-	V
			3.0 V	2.6	2.8	-	V
			4.5 V	4.2	4.4	-	V
		I <sub>O</sub> = -8 mA	2.3 V	1.4	1.7	-	V
			3.0 V	2.2	2.5	-	V
			4.5 V	3.9	4.1	-	V
		I <sub>O</sub> = -16 mA	3.0 V	1.5	2.0	-	V
4.5 V	3.3		3.8	-	V		
I <sub>O</sub> = -24 mA	4.5 V	3.0	3.5	-	V		
I <sub>CC</sub>	Supply current (quiescent)	V <sub>I</sub> = GND, $\overline{OE}$ = GND I <sub>O</sub> = 0 mA	5.5 V	-	100	150	μA
I <sub>I</sub>	Input current	V <sub>I</sub> = V <sub>CC</sub> or GND	1.65 to 5.5 V	-	-	±1	μA
I <sub>OZ</sub>	Output leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND $\overline{OE}$ = V <sub>CC</sub>	1.65 to 5.5 V	-	-	±5	μA
I <sub>OFF</sub>	Powerdown leakage current <sup>(1)</sup>	V <sub>I</sub> = V <sub>CC</sub> or GND	OFF <sup>(2)</sup>	-	-	5	μA

<sup>(1)</sup> into any input or output port

<sup>(2)</sup> V<sub>CC</sub> is at GND potential

## 5.4 DYNAMIC CHARACTERISTICS

All parameters are specified across the entire operating temperature range unless otherwise specified.

**Table 7:** AC Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	V <sub>CC</sub>	MIN	TYP	MAX	UNITS
$t_{pd}^{(1)}$	Propagation Delay (Input <b>A</b> to Output <b>B</b> or Input <b>B</b> to Output <b>A</b> )	$C_L = 50 \text{ pF}$	4.5 to 5.5 V	-	5	11	ns
			3.0 to 3.6 V	-	6.1	13	ns
			2.3 to 2.7 V	-	7.8	15	ns
			1.65 to 1.95 V	-	11.5	25	ns
$t_{en}^{(2)}$	Output Enable Time (Input <b>OE</b> to Output <b>A</b> or <b>B</b> )	$C_L = 50 \text{ pF}$	4.5 to 5.5 V	-	13.6	25	ns
			3.0 to 3.6 V	-	14.9	35	ns
			2.3 to 2.7 V	-	16.9	41	ns
			1.65 to 1.95 V	-	21.9	53	ns
$t_{dis}^{(3)}$	Output Disable Time (Input <b>OE</b> to Output <b>A</b> or <b>B</b> )	$C_L = 50 \text{ pF}$	4.5 to 5.5 V	-	14.4	25	ns
			3.0 to 3.6 V	-	15.7	35	ns
			2.3 to 2.7 V	-	17.5	40	ns
			1.65 to 1.95 V	-	21.3	51	ns
$t_{sk}$	Channel-to-channel skew	$C_L = 50 \text{ pF}$	1.65 to 5.5 V	-	-	1	ns
$C_{in}$	Input capacitance <sup>(4)</sup>	$V_I = V_{CC} \text{ or GND}$	1.65 to 5.5 V	-	2	4	pF
$C_{pd}$	Power dissipation capacitance <sup>(4)</sup>	$I_O = 0 \text{ mA}, f = 1 \text{ MHz}$	5.5 V	-	40	-	pF

- (1) equivalent to  $t_{PLH}$ ,  $t_{PHL}$
- (2) equivalent to  $t_{PZL}$ ,  $t_{PHL}$
- (3) equivalent to  $t_{PLZ}$ ,  $t_{PHZ}$
- (4) guaranteed by design

## 5.5 RADIATION RESILIENCE

For detailed radiation testing reports, please contact Apogee Semiconductor at [sales@apogeesemi.com](mailto:sales@apogeesemi.com).

**Table 8:** Radiation Resilience Characteristics

PARAMETER	CONDITIONS	VALUE	UNITS
Total Ionizing Dose (TID)	Please contact Apogee Semiconductor for test report.	30	krad (Si)
SEL Onset LET Threshold	Please contact Apogee Semiconductor for test report.	$\geq 80$	MeV-cm <sup>2</sup> /mg

5.6 CHARACTERISTICS MEASUREMENT INFORMATION

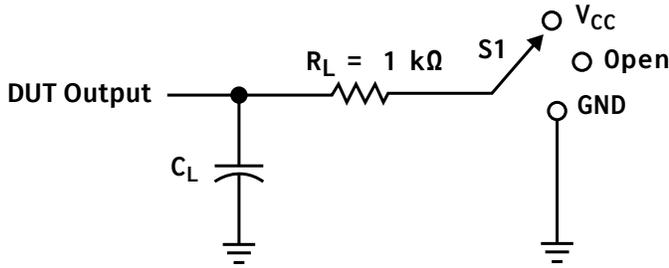


Figure 3: Load Circuit for 3-State Outputs

TEST	S1
$t_{pd}$	Open
$t_{PLZ}, t_{PZL}$	$V_{CC}$
$t_{PHZ}, t_{PZH}$	GND

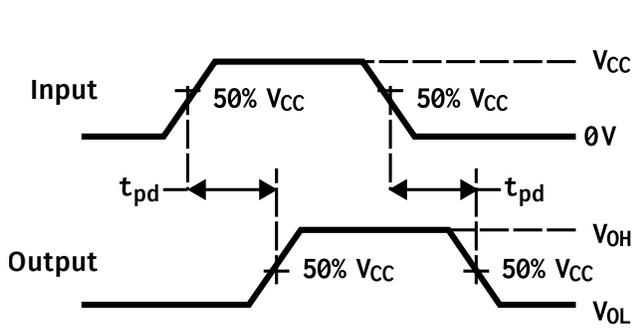


Figure 4: Propagation Delay Measurement

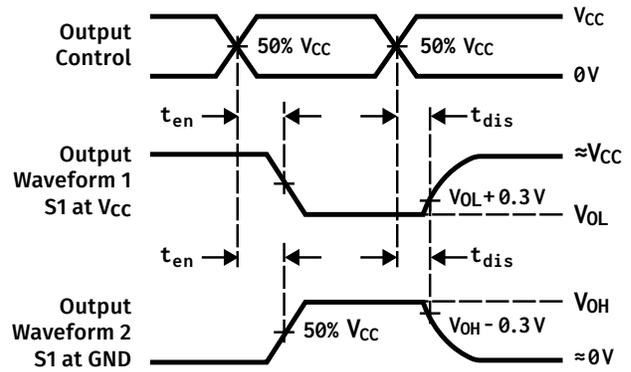


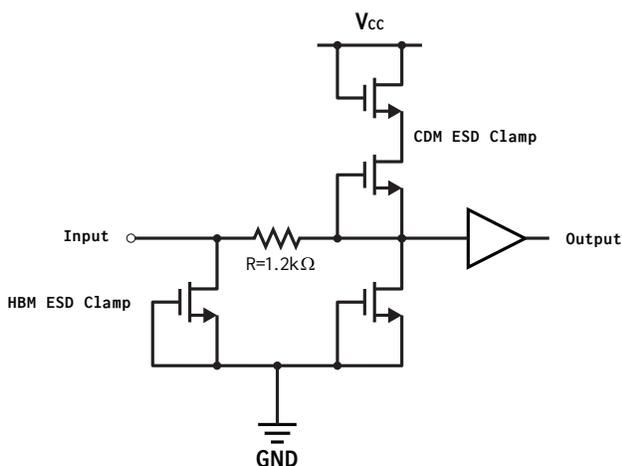
Figure 5: Enable and Disable Time Measurements

## 6 DETAILED DESCRIPTION

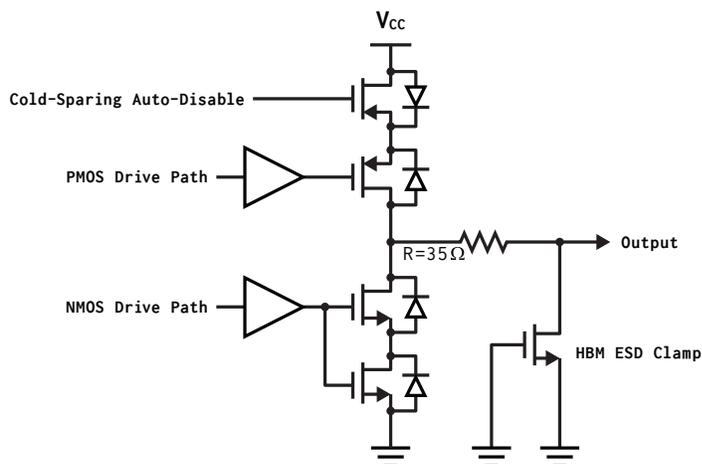
The AP54RHC506 is a 5-bit bus transceiver with 3-state outputs intended to perform the Boolean function **BUFF** ( $Y = A$ ) in positive logic. Designed to operate from a wide supply voltage of 1.65 to 5.5 V, it has fully redundant input and output stages providing for superior resiliency to single event effects.

The output and input stages are constructed with transient-activated clamps (Figure 6, 7) that prevent inadvertent biasing of the  $V_{CC}$  power rail through parasitic diodes inherent to conventional input, output, and ESD circuits. The IC also incorporates an internal power-on reset (POR) circuit that prevents the output from driving erroneous results during power-on, and guarantees correct operation at power supply voltages as low as 1.65 V. While the supply is ramping, the POR holds the output buffer in tri-state, a feature that prevents unwanted DC current during cold sparing on input and output pins.

The AP54RHC family's I/O protection circuitry allows for cold sparing configurations as it avoids a leakage current penalty on inputs and outputs while in a power-down state. This can result in considerable power savings in systems where multiple-path redundancy is employed. The ESD clamp circuits for this logic family are designed to support Class 2 ESD levels of 4 kV HBM and 500 V CDM.



**Figure 6:** Input Pin Structure



**Figure 7:** Output Pin Structure

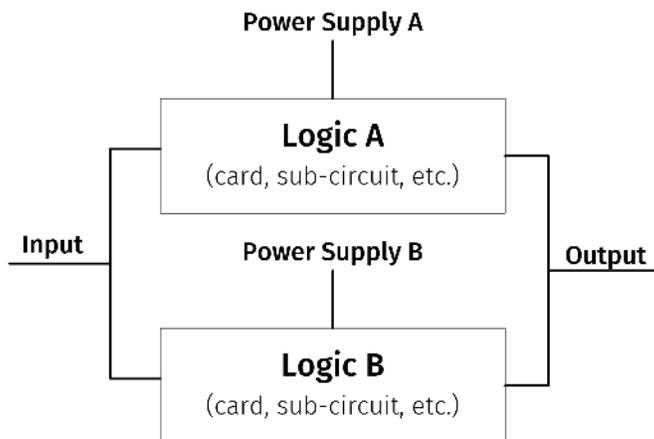
### Note

During tri-state, the application must ensure that the output pins are either held or switched to logic high or logic low levels i.e. close to  $V_{CC}$  or **GND**, otherwise increased supply current can occur.

## 7 APPLICATIONS INFORMATION

### 7.1 USE IN COLD-SPARING CONFIGURATION

As the AP54RHC family is radiation-hardened by design and includes internal TMR, it can be utilized in high-reliability applications without additional supporting circuitry or devices. Nonetheless, some application requirements call for fully-redundant designs, where an “A” and a “B” device are required, often on separate power rails.



**Figure 8:** Two-Path Cold-Sparing Configuration

With the cold sparing capability of the AP54RHC family, fully redundant “A” and “B” functions may be placed in parallel (as seen in Figure 8) running off redundant power supplies. The inputs and outputs on each one of these functions are assumed to be based on the AP54RHC family, allowing for direct parallel connection without unwanted leakage current paths during cold sparing. In the event of a failure in power supply A or within function A, the system can simply shut power supply A off and switch on power supply B, without requiring additional input or output switching or configuration changes.

### 7.2 POWER SUPPLY RECOMMENDATIONS

This device can operate at any voltage within the range specified in [Table 4 Recommended Operating Conditions](#).

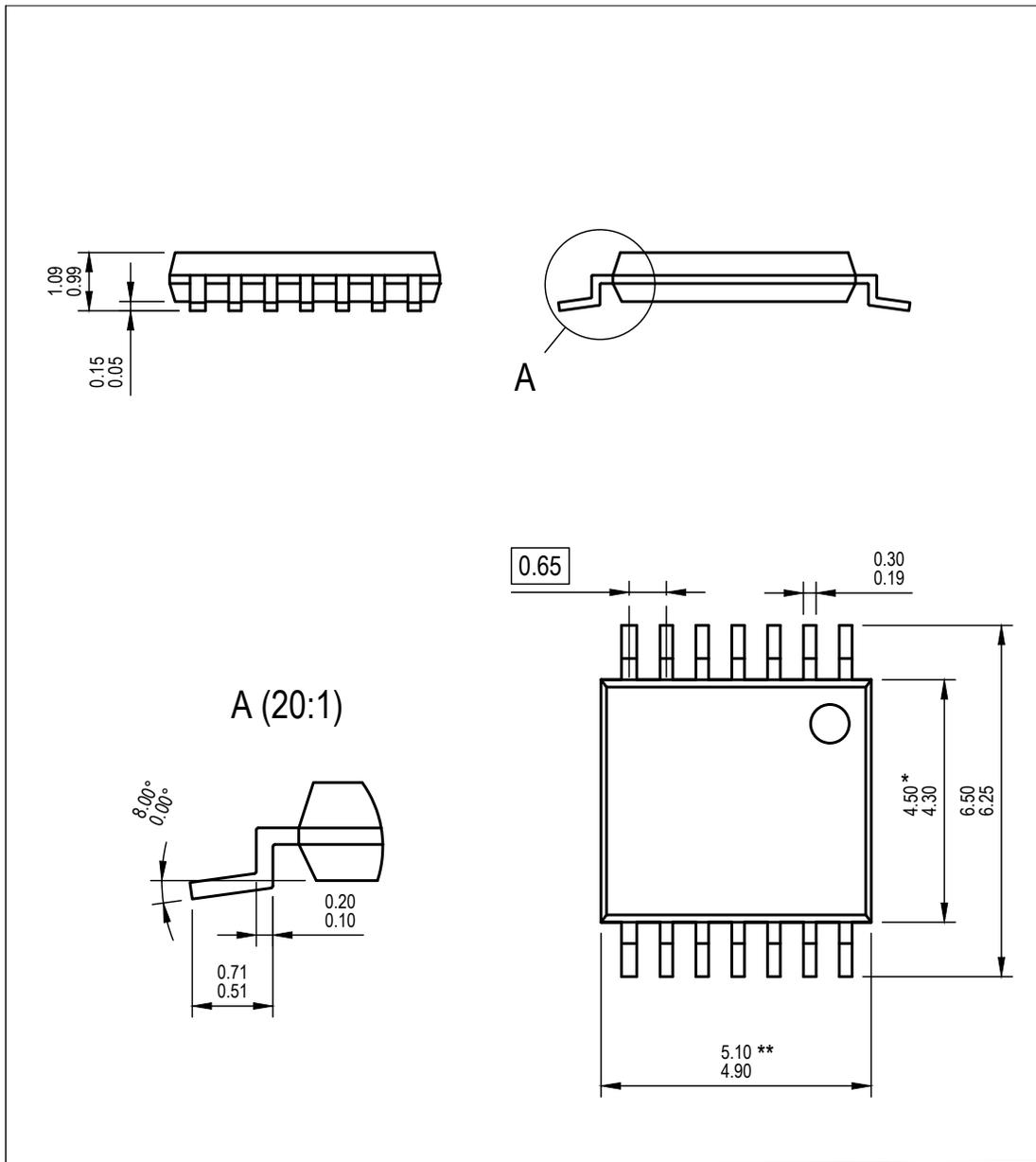
At a minimum, a 16 VDC (or higher), X7R-rated 0.1  $\mu$ F ceramic decoupling capacitor should be placed near (within 1 cm) the  $V_{CC}$  pin of the device.

### 7.3 APPLICATION TIPS

Unused **inputs** must **not** be left floating. They may be connected to either a low (GND) or high ( $V_{CC}$ ) bias to provide a known state at the input of the device. Resistors may be used to tie off unused inputs. In the event of a design change, such resistors can be removed, thereby allowing use of the inputs without having to cut traces on the PCB.

An unused **output** may be left unconnected. However, if the output is held in tristate, it is recommended to weakly bias the output to a valid logic level to prevent increased supply current. It is suggested that it be routed to a test point or similar accessible structure in case the associated function needs to be utilized as part of a design revision.

## 8 PACKAGING INFORMATION



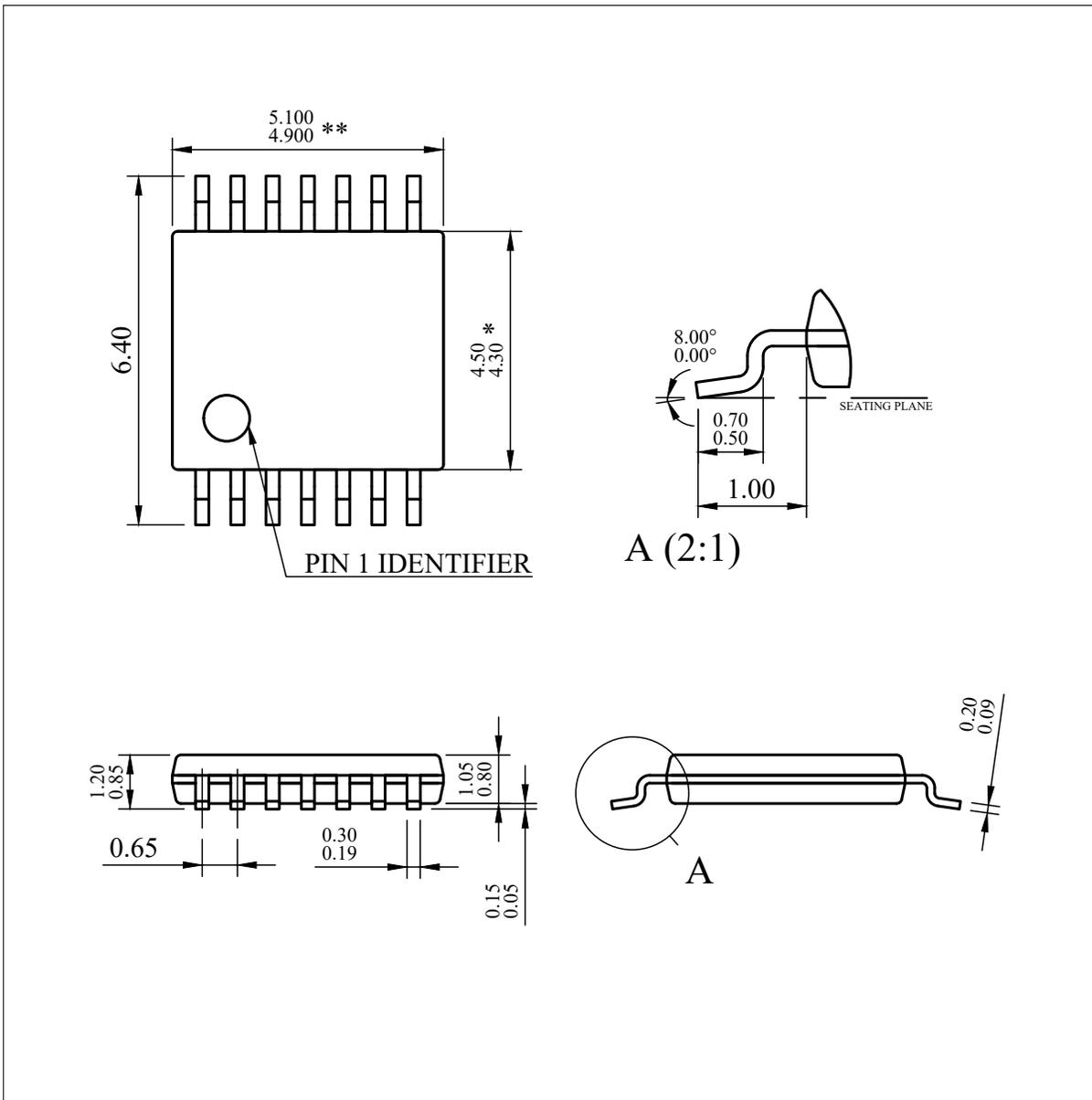
**Notes:**

1. All linear dimensions are in millimeters. Dimensioning and tolerancing are as per ISO/TS 128-71:2010
2. The part is compliant with JEDEC MO-153 specifications.

\* Body width does **not** include interlead flash. Interlead flash shall not exceed 0.25 mm each side.

\*\* Body length does **not** include mold flash, protrusion, or gate burrs. Mold flash, protrusions, and gate burrs shall not exceed 0.15 mm on each side.

**Figure 9: 14-LT - Package Mechanical Drawing (SnPb)**



Notes:

1. All linear dimensions are in millimeters. Dimensioning and tolerancing are as per ISO/TS 128-71:2010
2. The part is compliant with JEDEC MO-153 specifications.

\* Body width does **not** include interlead flash. Interlead flash shall not exceed 0.25 mm each side.

\*\* Body length does **not** include mold flash, protrusion, or gate burrs. Mold flash, protrusions, and gate burrs shall not exceed 0.15 mm on each side.

Figure 10: 14-NT - Package Mechanical Drawing (NiPdAu)

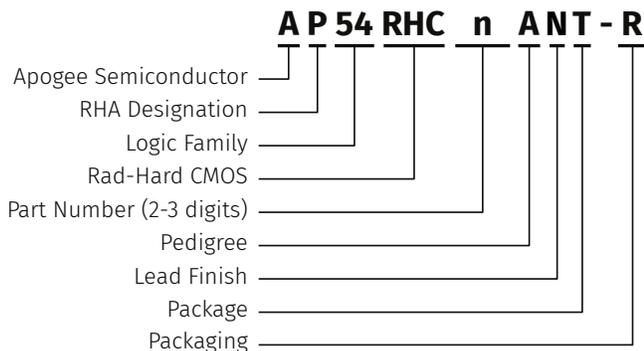
## 9 ORDERING INFORMATION

Example part numbers for the AP54RHC506 are listed in Table 9. The full list of options for this part can be found in Figure 11. For a detailed description of product grades, please refer to [Product Grades and Quality Flows document](#). Please contact Apogee Semiconductor sales at [sales@apogeesemi.com](mailto:sales@apogeesemi.com) for further information on sampling, lead time and purchasing on specific part numbers.

**Table 9:** AP54RHC506 Ordering Information

DEVICE	DESCRIPTION	PACKAGE	LEAD FINISH	PACKAGE DIAGRAM	PACKAGE MASS
AP54RHC506ALT-R	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	SnPb	14-LT	47 mg
AP54RHC506ALT-J <sup>(1)</sup>	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	SnPb	14-LT	47 mg
AP54RHC506BLT-R	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	SnPb	14-LT	47 mg
AP54RHC506BLT-J <sup>(1)</sup>	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	SnPb	14-LT	47 mg
AP54RHC506CLT-R	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	SnPb	14-LT	47 mg
AP54RHC506CLT-J <sup>(1)</sup>	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	SnPb	14-LT	47 mg
AP54RHC506ELT-R	Rad-Hard 5-Channel Bus Transceiver (for eval only)	TSSOP-14	SnPb	14-LT	47 mg
AP54RHC506ELT-J <sup>(1)</sup>	Rad-Hard 5-Channel Bus Transceiver (for eval only)	TSSOP-14	SnPb	14-LT	47 mg
AP54RHC506ANT-R	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	NiPdAu	14-NT	58 mg
AP54RHC506ANT-J <sup>(1)</sup>	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	NiPdAu	14-NT	58 mg
AP54RHC506BNT-R	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	NiPdAu	14-NT	58 mg
AP54RHC506BNT-J <sup>(1)</sup>	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	NiPdAu	14-NT	58 mg
AP54RHC506CNT-R	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	NiPdAu	14-NT	58 mg
AP54RHC506CNT-J <sup>(1)</sup>	Rad-Hard 5-Channel Bus Transceiver (30 krad (Si))	TSSOP-14	NiPdAu	14-NT	58 mg
AP54RHC506ENT-R	Rad-Hard 5-Channel Bus Transceiver (for eval only)	TSSOP-14	NiPdAu	14-NT	58 mg
AP54RHC506ENT-J <sup>(1)</sup>	Rad-Hard 5-Channel Bus Transceiver (for eval only)	TSSOP-14	NiPdAu	14-NT	58 mg

<sup>(1)</sup> Available through distributors only.



**Figure 11:** Part Number Decoder

1. RHA Designation
  - P** 30 krad (Si)
  - F** 300 krad (Si)
2. Part Number
  - 506** (5-Channel Bus Transceiver)
3. Pedigree
  - A** -55 to +125 °C (Burn-in)
  - B** -55 to +125 °C (No burn-in)
  - C** 25 °C (No burn-in)
  - E** 25 °C Functional Test Only (Evaluation)
4. Lead Finish
  - L** Tin-Lead (SnPb)
  - N** Nickel-Palladium-Gold (NiPdAu)
5. Package
  - T** 14-pin Thin Shrink Small Outline Package (TSSOP)
6. Packaging
  - R** Tape and Reel<sup>(1)</sup>
  - J** JEDEC Tray

<sup>(1)</sup> [Contact us](#) for custom reel quantities. Orders less than full reel quantities may be shipped as cut tape.

## 10 REVISION HISTORY

REVISION	DESCRIPTION	DATE
A07	Updated ordering information.	2025-09-02
A06	Rename $\overline{EN}$ (enabled) to $\overline{OE}$ (output enabled). Updated detailed description note. Add 4mA row for $V_{CC}=1.65\text{ V}$ for $V_{OH}$ . Add NiPdAu packaging option. Added outgassing feature bullet. Added package mass. Corrected test symbol for Output leakage current in Table 6 to $I_{oz}$ . Updated values in static characteristics (Table 6). Updated typical timings in table 7. Updated description.	2024-09-10
A05	Correct output pin structure diagram.	2021-12-06
A04	Updated ordering information.	2021-07-30
A03	Update and clean-up of static and dynamic characteristics.	2021-06-23
A02	Update Static and Dynamic characteristics.	2020-08-07
A01	Initial public release.	2020-02-29
A00	Initial internal release.	2019-07-05

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